

# Anthony Levi

## List of Publications by Year in descending order

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174  
papers

6,840  
citations

76196

40  
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64668

79  
g-index

183  
all docs

183  
docs citations

183  
times ranked

4189  
citing authors

#	ARTICLE	IF	CITATIONS
1	Whispering-gallery mode microdisk lasers. Applied Physics Letters, 1992, 60, 289-291.	1.5	1,335
2	Graphene-Silicon Schottky Diodes. Nano Letters, 2011, 11, 1863-1867.	4.5	435
3	Threshold characteristics of semiconductor microdisk lasers. Applied Physics Letters, 1993, 63, 1310-1312.	1.5	241
4	Injected-Hot-Electron Transport in GaAs. Physical Review Letters, 1985, 55, 2071-2073.	2.9	218
5	Origin of the Excess Capacitance at Intimate Schottky Contacts. Physical Review Letters, 1988, 60, 53-56.	2.9	202
6	Schottky-barrier inhomogeneity at epitaxial NiSi <sub>2</sub> interfaces on Si(100). Physical Review Letters, 1991, 66, 72-75.	2.9	183
7	Directional light coupling from microdisk lasers. Applied Physics Letters, 1993, 62, 561-563.	1.5	174
8	Transistor action in Si/CoSi <sub>2</sub> /Si heterostructures. Applied Physics Letters, 1985, 47, 151-153.	1.5	171
9	Ion-beam-induced metal-insulator transition in YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-<math>\delta</math></sub> : A mobility edge. Physical Review B, 1989, 39, 11599-11602.	1.1	144
10	Hot-Electron Spectroscopy of GaAs. Physical Review Letters, 1985, 54, 1570-1572.	2.9	140
11	Control of a natural permeable CoSi <sub>2</sub> base transistor. Applied Physics Letters, 1986, 48, 635-637.	1.5	127
12	Room-temperature operation of hot-electron transistors. Applied Physics Letters, 1987, 51, 984-986.	1.5	114
13	Ion-beam-induced destruction of superconducting phase coherence in YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-<math>\delta</math></sub> . Physical Review B, 1988, 37, 3755-3758.	1.1	100
14	Controllable reduction of critical currents in YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-<math>\delta</math></sub> films. Applied Physics Letters, 1988, 53, 1010-1012.	1.5	98
15	Three-dimensional imaging of integrated circuits with macro- to nanoscale zoom. Nature Electronics, 2019, 2, 464-470.	13.1	96
16	Tunneling in the presence of phonons: A solvable model. Physical Review Letters, 1989, 62, 1683-1686.	2.9	88
17	Schottky-barrier heights of single-crystal NiSi <sub>2</sub> on Si(111): The effect of a surface-n-junction. Physical Review B, 1986, 33, 7077-7090.	1.1	83
18	Picosecond pump and probe spectroscopy utilizing freely propagating terahertz radiation. Optics Letters, 1991, 16, 48.	1.7	81

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19	Normal-state transport parameters of epitaxial thin films of $\text{YBa}_2\text{Cu}_3\text{O}_7$ . <i>Physical Review B</i> , 1988, 38, 2472-2476.	1.1	80
20	Room-temperature lasing action in $\text{In}_{0.51}\text{Ga}_{0.49}\text{P}/\text{In}_{0.2}\text{Ga}_{0.8}\text{As}$ microcylinder laser diodes. <i>Applied Physics Letters</i> , 1993, 62, 2021-2023.	1.5	80
21	The spectrum of microdisk lasers. <i>Journal of Applied Physics</i> , 1996, 80, 644-653.	1.1	74
22	Preparation of superconducting thin films of calcium strontium bismuth copper oxides by coevaporation. <i>Applied Physics Letters</i> , 1988, 52, 1828-1830.	1.5	73
23	Nonequilibrium electron transport in bipolar devices. <i>Applied Physics Letters</i> , 1987, 51, 42-44.	1.5	70
24	Direct observation of two-dimensional magnetopolarons in a resonant tunnel junction. <i>Physical Review Letters</i> , 1990, 65, 235-238.	2.9	70
25	Resonant modes and laser spectrum of microdisk lasers. <i>Applied Physics Letters</i> , 1995, 66, 2932-2934.	1.5	70
26	Electrical response of superconducting $\text{YBa}_2\text{Cu}_3\text{O}_7$ to light. <i>Applied Physics Letters</i> , 1989, 54, 1175-1177.	1.5	69
27	MAUI: Enabling Fiber-to-the-Processor With Parallel Multiwavelength Optical Interconnects. <i>Journal of Lightwave Technology</i> , 2004, 22, 2043-2054.	2.7	68
28	Pair-breaking description of the vortex-depinning critical field in $\text{YBa}_2\text{Cu}_3\text{O}_7$ thin films. <i>Physical Review B</i> , 1989, 40, 5243-5246.	1.1	64
29	Very low threshold $\text{InGaAs}/\text{InGaAsP}$ graded index separate confinement heterostructure quantum well lasers grown by atmospheric pressure metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , 1989, 55, 2283-2285.	1.5	57
30	Nonrandom doping and elastic scattering of carriers in semiconductors. <i>Applied Physics Letters</i> , 1989, 54, 940-942.	1.5	56
31	$\text{Si}(100)$ $(2\text{\AA}-1)$ boron reconstruction: Self-limiting monolayer doping. <i>Applied Physics Letters</i> , 1990, 57, 2779-2781.	1.5	54
32	Near-ideal lateral scaling in abrupt $\text{Al}_{0.48}\text{In}_{0.52}\text{As}/\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ heterostructure bipolar transistors prepared by molecular beam epitaxy. <i>Applied Physics Letters</i> , 1989, 54, 2333-2335.	1.5	52
33	Large nonlinear phase shifts in low-loss $\text{Al}_x\text{Ga}_{1-x}\text{As}$ waveguides near half-gap. <i>Applied Physics Letters</i> , 1991, 59, 2558-2560.	1.5	51
34	Nonlinear spectroscopy near half-gap in bulk and quantum well $\text{GaAs}/\text{AlGaAs}$ waveguides. <i>Journal of Applied Physics</i> , 1992, 71, 1927-1935.	1.1	50
35	Ballistic injection devices in semiconductors. <i>Applied Physics Letters</i> , 1986, 48, 1609-1611.	1.5	48
36	Epitaxial yttrium silicide on (111) silicon by vacuum annealing. <i>Applied Physics Letters</i> , 1987, 51, 311-313.	1.5	48

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37	Ion beam thinning and polishing of YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7</sub> films. Applied Physics Letters, 1989, 55, 1915-1917.	1.5	44
38	High index contrast mirrors for optical microcavities. Applied Physics Letters, 1990, 57, 1387-1389.	1.5	44
39	Log $\epsilon$ -periodic antennas for pulsed terahertz radiation. Applied Physics Letters, 1991, 59, 262-264.	1.5	44
40	Growth of strained $\epsilon$ -layer semiconductor $\epsilon$ -metal $\epsilon$ -semiconductor heterostructures. Applied Physics Letters, 1986, 48, 1264-1266.	1.5	42
41	Vertical scaling in heterojunction bipolar transistors with nonequilibrium base transport. Applied Physics Letters, 1992, 60, 460-462.	1.5	42
42	Optimization of aperiodic dielectric structures. Journal of Applied Physics, 2006, 100, 034310.	1.1	40
43	Gate tunable graphene-silicon Ohmic/Schottky contacts. Applied Physics Letters, 2012, 101, .	1.5	40
44	Nanoscale x-ray imaging of circuit features without wafer etching. Physical Review B, 2017, 95, .	1.1	40
45	On the temperature sensitivity of semiconductor lasers. Applied Physics Letters, 1992, 60, 157-159.	1.5	39
46	Epitaxial metal $\epsilon$ -semiconductor structures and their properties. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1986, 4, 1435.	1.6	38
47	Gigabyte/s data communications with the POLO parallel optical link. , 0, , .		37
48	Temperature dependence of long wavelength semiconductor lasers. Applied Physics Letters, 1992, 60, 1058-1060.	1.5	36
49	Ultrafast coplanar air $\epsilon$ -transmission lines. Applied Physics Letters, 1990, 57, 1123-1125.	1.5	34
50	$\epsilon$ - $\epsilon$ -Coreless defects $\epsilon$ - $\epsilon$ and the continuity of epitaxial NiSi <sub>2</sub> /Si(100) thin films. Applied Physics Letters, 1988, 52, 828-830.	1.3	32
51	Base doping limits in heterostructure bipolar transistors. Applied Physics Letters, 1990, 56, 1460-1462.	1.5	31
52	14.6-GHz LiNbO <sub>3</sub> /sub 3/ microdisk photonic self-homodyne RF receiver. IEEE Transactions on Microwave Theory and Techniques, 2006, 54, 821-831.	2.9	31
53	Base transport dynamics in a heterojunction bipolar transistor. Applied Physics Letters, 1986, 49, 1481-1483.	1.5	29
54	Self-homodyne RF-optical LiNbO <sub>3</sub> microdisk receiver. Solid-State Electronics, 2005, 49, 1428-1434.	0.8	29

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55	Dynamic and static response of multielectrode lasers. <i>Applied Physics Letters</i> , 1990, 57, 968-970.	1.5	26
56	Extreme nonequilibrium electron transport in heterojunction bipolar transistors. <i>Applied Physics Letters</i> , 1988, 52, 2247-2249.	1.5	25
57	Electromagnetic Response of Broken-Symmetry Nanoscale Clusters. <i>Physical Review Letters</i> , 2006, 97, 036806.	2.9	25
58	AlAs/GaAs tunnel emitter bipolar transistor. <i>Applied Physics Letters</i> , 1989, 54, 2250-2252.	1.5	24
59	Aperiodic nanophotonic design. <i>Journal of Applied Physics</i> , 2004, 95, 1420-1426.	1.1	24
60	Quantum Fluctuations in Small Lasers. <i>Physical Review Letters</i> , 2009, 102, 053902.	2.9	24
61	States at epitaxial NiSi <sub>2</sub> /Si heterojunctions studied by deep-level transient spectroscopy and hydrogenation. <i>Physical Review B</i> , 1986, 34, 4415-4418.	1.1	23
62	Electrical conduction in the Si(111):B-( $\hat{\sigma}$ — $\hat{\sigma}$ ) <sup>30</sup> /a-Si interface reconstruction. <i>Physical Review B</i> , 1991, 43, 14711-14714.	1.1	23
63	Electron-transport dynamics in quantized intrinsic GaAs. <i>Physical Review B</i> , 1987, 36, 9402-9405.	1.1	22
64	Bias-controlled intersubband wavelength switching in a GaAs/AlGaAs quantum well laser. <i>Applied Physics Letters</i> , 1989, 55, 1382-1384.	1.5	22
65	High-field transport in GaAs transistors. <i>Applied Physics Letters</i> , 1989, 54, 813-815.	1.5	21
66	Ordered monolayer structures of boron in Si(111) and Si(100). <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1991, 9, 2269-2272.	0.9	21
67	High-frequency study of nonequilibrium transport in heterostructure bipolar transistors. <i>Applied Physics Letters</i> , 1989, 55, 1789-1791.	1.5	20
68	Nonequilibrium electron transport in heterostructure bipolar transistors probed by magnetic field. <i>Applied Physics Letters</i> , 1990, 56, 2660-2662.	1.5	20
69	Polarization of lasing emission in microdisk laser diodes. <i>Applied Physics Letters</i> , 1995, 66, 1859-1861.	1.5	20
70	Electroluminescence from the base of a GaAs/AlGaAs double heterojunction bipolar transistor. <i>Applied Physics Letters</i> , 1987, 50, 98-100.	1.5	19
71	Numerical study of nonequilibrium electron transport in AlGaAs/GaAs heterojunction bipolar transistors. <i>Applied Physics Letters</i> , 1989, 55, 250-252.	1.5	19
72	Multielectrode quantum well laser for digital switching. <i>Applied Physics Letters</i> , 1990, 56, 1095-1097.	1.5	19

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73	Ultrahigh-Speed Bipolar Transistors. <i>Physics Today</i> , 1990, 43, 58-64.	0.3	18
74	Saturable absorption in intracavity loss modulated quantum well lasers. <i>Applied Physics Letters</i> , 1991, 59, 16-18.	1.5	18
75	Optimal control of electromagnetic field using metallic nanoclusters. <i>New Journal of Physics</i> , 2008, 10, 043017.	1.2	18
76	Plasmonic excitations in tight-binding nanostructures. <i>Physical Review B</i> , 2009, 80, .	1.1	17
77	GaInAs/GaInAsP/InP heterostructure bipolar transistors with very thin base (150 Å...) grown by chemical beam epitaxy. <i>Applied Physics Letters</i> , 1988, 53, 983-985.	1.5	16
78	Wavelength switching in InGaAs/InP quantum well lasers. <i>Applied Physics Letters</i> , 1990, 56, 122-124.	1.5	16
79	Low-threshold GaAs/AlGaAs quantum-well lasers grown by organometallic vapor-phase epitaxy using trimethylamine alane. <i>Journal of Applied Physics</i> , 1991, 70, 432-435.	1.1	16
80	Comparison of graded and abrupt junction In <sub>0.53</sub> Ga <sub>0.47</sub> As heterojunction bipolar transistors. <i>Applied Physics Letters</i> , 1994, 64, 67-69.	1.5	16
81	Electron transport in an AlSb/InAs/GaSb tunnel emitter hot-electron transistor. <i>Applied Physics Letters</i> , 1989, 55, 1891-1893.	1.5	15
82	Polarization-dependent reflectivity from dielectric nanowires. <i>Applied Physics Letters</i> , 2003, 83, 996-998.	1.5	15
83	Adaptive design of excitonic absorption in broken-symmetry quantum wells. <i>Applied Physics Letters</i> , 2004, 85, 121-123.	1.5	15
84	Quantum fluctuations in very small laser diodes. <i>Physical Review A</i> , 2010, 81, .	1.0	15
85	Adaptive design of nanoscale dielectric structures for photonics. <i>Journal of Applied Physics</i> , 2003, 94, 6065-6068.	1.1	14
86	Synthesis of electron transmission in nanoscale semiconductor devices. <i>Applied Physics Letters</i> , 2006, 88, 013502.	1.5	14
87	A Novel Formulation of the Adjoint Method in the Optimal Design of Quantum Electronic Devices. <i>SIAM Journal on Control and Optimization</i> , 2010, 48, 3191-3223.	1.1	14
88	Towards Quantum Engineering. <i>Proceedings of the IEEE</i> , 2008, 96, 335-342.	16.4	13
89	Phonon structure of amorphous germanium by inelastic electron tunnelling spectroscopy. <i>Journal of Physics C: Solid State Physics</i> , 1984, 17, 1643-1653.	1.5	12
90	Direct observation of the electron spectral function in the integer and fractional quantum Hall regimes by resonant tunneling. <i>Physical Review B</i> , 1993, 47, 16608-16611.	1.1	12

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91	Magnetic field dependence of hot-electron transport in GaAs. Applied Physics Letters, 1985, 47, 964-966.	1.5	11
92	Voltage-controlled Q-switching of InGaAs/InP single quantum well lasers. Applied Physics Letters, 1989, 55, 1940-1942.	1.5	11
93	Inelastic scattering of electrons traversing semiconductor heterojunctions. Applied Physics Letters, 1988, 52, 236-238.	1.5	10
94	Carrier pinning by mode fluctuations in laser diodes. Applied Physics Letters, 1993, 62, 1454-1456.	1.5	10
95	Quantum reflections and inelastic scattering of electrons in semiconductor heterostructures. Physical Review B, 1988, 38, 9843-9849.	1.1	9
96	Forward transit delay in In <sub>0.53</sub> /Ga <sub>0.47</sub> /As heterojunction bipolar transistors with nonequilibrium electron transport. IEEE Transactions on Electron Devices, 1993, 40, 1942-1949.	1.6	9
97	Adaptive quantum design of atomic clusters. Physical Review B, 2004, 69, .	1.1	9
98	Quantum fluctuations and saturable absorption in mesoscale lasers. Physical Review A, 2011, 83, .	1.0	9
99	Cavity formation in semiconductor lasers. Applied Physics Letters, 1992, 61, 889-891.	1.5	8
100	InGaAs/GaAs quantum well lasers with dry-etched mirror passivated by vacuum atomic layer epitaxy. Applied Physics Letters, 1994, 65, 1748-1750.	1.5	8
101	Transferred-electron induced current instabilities in heterojunction bipolar transistors. Applied Physics Letters, 1995, 66, 3319-3321.	1.5	8
102	Dynamics of injected electron cooling in GaAs. Applied Physics Letters, 1986, 48, 1365-1367.	1.5	7
103	Hot Electron Transistors Using Si/CoSi <sub>2</sub> . Materials Research Society Symposia Proceedings, 1987, 107, 259.	0.1	7
104	Large-signal picosecond response of InGaAs/InP quantum well lasers with an intracavity loss modulator. Applied Physics Letters, 1990, 56, 1629-1631.	1.5	7
105	Ring resonator-based photonic microwave receiver modulator with picowatt sensitivity. IET Optoelectronics, 2011, 5, 36-39.	1.8	7
106	Hot Electron Transistors Using Si/CoSi <sub>2</sub> . Materials Research Society Symposia Proceedings, 1987, 102, 361.	0.1	6
107	Wavelength dependence of TO in InGaAsP semiconductor laser diodes. Applied Physics Letters, 1993, 62, 2009-2011.	1.5	6
108	Transient response of wavelength switching in multicavity mode-locked laser diodes. Applied Physics Letters, 1996, 69, 3647-3649.	1.5	6

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109	Self-homodyne photonic microwave receiver architecture based on linear optical modulation and filtering. Microwave and Optical Technology Letters, 2008, 50, 345-350.	0.9	6
110	Asymmetric line broadening in intracavity loss modulated quantum well distributed feedback lasers. Applied Physics Letters, 1991, 58, 669-671.	1.5	5
111	Forward delay in scaled Al <sub>0.48</sub> In <sub>0.52</sub> As/In <sub>0.53</sub> Ga <sub>0.47</sub> As heterojunction bipolar transistors. Applied Physics Letters, 1993, 63, 2231-2233.	1.5	5
112	Comparison of plasma chemistries for patterning InP-based laser structures. Plasma Sources Science and Technology, 1994, 3, 19-24.	1.3	5
113	Wavelength switching in multicavity lasers. Applied Physics Letters, 1997, 71, 300-302.	1.5	5
114	Epitaxial NiSi <sub>2</sub> and CoSi <sub>2</sub> Interfaces. NATO ASI Series Series B: Physics, 1989, , 167-181.	0.2	5
115	Electron Transport Through Epitaxial Metal/Semiconductor Heterostructures. Materials Research Society Symposia Proceedings, 1986, 77, 271.	0.1	4
116	Unipolar Hot Electron Transistors. Physica Scripta, 1988, T23, 227-231.	1.2	4
117	All-optical timing restoration using a hybrid time-domain chirp switch. Optics Letters, 1991, 16, 1116.	1.7	4
118	Optimal design of heterostructure tunnel diode with nonlinear current-voltage characteristic. Physica E: Low-Dimensional Systems and Nanostructures, 2012, 44, 1503-1509.	1.3	4
119	Summary Abstract: Hot-electron transport in the AlSb/InAs/GaSb double heterostructure prepared by molecular-beam epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1988, 6, 674.	1.6	3
120	Quantification and control of non-Markovian evolution in finite quantum systems via feedback. Physical Review A, 2014, 89, .	1.0	3
121	Single Crystal NiSi <sub>2</sub> /Si Interfaces: Fabrication, Structures, and Schottky Barrier Heights. Materials Research Society Symposia Proceedings, 1991, 221, 71.	0.1	2
122	<title>Temperature dependence of semiconductor lasers (Invited Paper)</title>. , 1992, , .		2
123	<title>GeSi infrared photodetectors grown by rapid thermal CVD</title>. , 1993, , .		2
124	<title>Video broadcast using an optically controlled serially fed phased-array antenna</title>. , 1996, 2844, 258.		2
125	A multistate external cavity laser diode. Applied Physics Letters, 1998, 72, 2214-2216.	1.5	2
126	Design of resonators using materials with negative refractive index. Journal of the Optical Society of America B: Optical Physics, 2007, 24, 2791.	0.9	2



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127	Optimal design of a semiconductor heterostructure tunnel diode with linear current-voltage characteristic. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2011, 44, 322-326.	1.3	2
128	Coherent control of non-Markovian photon-resonator dynamics. <i>Physical Review A</i> , 2014, 90, .	1.0	2
129	Dynamic optoelectronic read/write memory. <i>Applied Physics Letters</i> , 1990, 56, 1501-1503.	1.5	1
130	<title>Microdisk lasers</title>. , 1994, , .		1
131	Active microdisk devices. , 2000, 3947, 185.		1
132	Accessing transmission-mode dispersion in super-prisms. <i>Solid-State Electronics</i> , 2003, 47, 1369-1377.	0.8	1
133	Synthesis for semiconductor device design. <i>Journal of Applied Physics</i> , 2005, 98, 044508.	1.1	1
134	Quantum and semiclassical inelastic electron transport. <i>Physical Review B</i> , 2010, 81, .	1.1	1
135	Supersymmetry with self-consistent Schrödinger-Poisson equations: finding partner potentials and breaking symmetry. <i>New Journal of Physics</i> , 2021, 23, 063026.	1.2	1
136	Hot Electron Transistors. <i>Springer Series in Electrophysics</i> , 1986, , 19-23.	0.2	1
137	Semiconductor microlasers. <i>Physics World</i> , 1993, 6, 32-35.	0.0	0
138	Where next for laser diodes?. <i>Physics World</i> , 1996, 9, 20-22.	0.0	0
139	The effect of scaling microlasers on modal noise. <i>Applied Physics Letters</i> , 1996, 69, 3459-3461.	1.5	0
140	Wavelength switching in multi-cavity laser diodes. <i>Journal of Applied Physics</i> , 1998, 84, 1805-1812.	1.1	0
141	<title>Intelligent monitoring and communication system</title>. , 2000, 3995, 566.		0
142	Electro-optic bistability in a LiNbO3 microdisk resonator. <i>IET Optoelectronics</i> , 2008, 2, 111-114.	1.8	0
143	Frontiers in device engineering: synthesis for nonintuitive design. <i>Proceedings of SPIE</i> , 2008, , .	0.8	0
144	Frontiers in device engineering. , 2009, , 1-31.		0

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145	Atoms-up design. , 2009, , 32-50.		0
146	Electron devices and electron transport. , 2009, , 51-87.		0
147	Aperiodic dielectric design. , 0, , 88-122.		0
148	Design at the classicalâ€“quantum boundary. , 2009, , 123-148.		0
149	Robust optimization in high dimensions. , 2009, , 149-188.		0
150	Mathematical framework for optimal design. , 2009, , 189-245.		0
151	Photonic microwave down-conversion based on linear modulation and filtering. , 2011, , .		0
152	Behavioral regimes and long-lived emitter states in mesolasers. Journal of Physics B: Atomic, Molecular and Optical Physics, 2019, 52, 245401.	0.6	0
153	Quantum Behavior in Mesoscale Lasers. , 2019, , .		0
154	Density of states and particle statistics. , 2020, , 1-20.		0
155	Toward Quantum Engineering. , 2020, , 1-10.		0
156	Expectation value $\langle \hat{n} \rangle$ . , 2020, , 1-4.		0
157	Non-Equilibrium Minority Carrier Transport. , 2020, , 1-24.		0
158	Physical Values. , 2020, , 1-2.		0
159	Semiconductors and Quantized States. , 2020, , 1-34.		0
160	Supersymmetry with scattering states. Europhysics Letters, 0, , .	0.7	0
161	Behavior of lasers in the small particle number limit. , 2009, , .		0
162	Phonon Structure of Amorphous Germanium by Inelastic Electron Tunnelling Spectroscopy. , 1985, , 913-916.		0

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163	High Speed Limits of Coplanar Transmission Lines. , 1993, , .		0
164	Throughput optimization for multimedia applications over high speed networks. , 1997, , 101-114.		0
165	Optimal heterostructure device design. , 2020, , 1-14.		0
166	The Boltzmann transport equation. , 2020, , 1-6.		0
167	Non-equilibrium electron scattering in n-type semiconductors. , 2020, , 1-32.		0
168	Semiclassical Electron Transport. , 2020, , 1-24.		0
169	Graphene. , 2020, , 1-6.		0
170	Electron Transmission. , 2020, , 1-28.		0
171	Electron-Phonon Scattering in Semiconductors. , 2020, , 1-20.		0
172	The Lindhard dielectric function. , 2020, , 1-12.		0
173	Crystal systems and the reciprocal lattice. , 2020, , 1-4.		0
174	Permittivity and effective potential in the linear response approximation. , 2020, , 1-2.		0